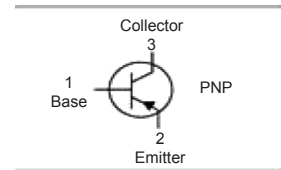


PNP Silicon Epitaxial Planar Transistor



Features:

- Power dissipation.(Pc = 200mW)
- Epitaxial planar die construction.
- Complementary NPN type MMST2222A



SOT-323

Application:

- General purpose application.

Maximum Rating @ TA = 25°C unless otherwise specified

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V _{CB0}	-60	V
Collector-Emitter Voltage	V _{CEO}	-60	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current -Continuous	I _C	-600	mA
Collector Dissipation	P _C	200	mW
Thermal resistance, junction to ambient	R _{θJA}	625	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

Electrical Characteristics @ TA = 25°C unless otherwise specified

Parameter	Symbol	Test conditions	Min.	Max.	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-10μA, I _E =0	-60		V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-10mA, I _B =0	-60		V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-10μA, I _C =0	-5		V
Collector cut-off current	I _{CBO}	V _{CB} =-50V, I _E =0		-10	nA
Collector cut-off current	I _{CEX}	V _{CE} =-30V, V _{EB(OFF)} =-0.5V		-50	nA
Base cut-off current	I _{BL}	V _{CE} =-30V, V _{EB(OFF)} =-0.5V		-50	nA
DC current gain	h _{FE}	V _{CE} =-10V, I _C =-0.1mA	75	-	
		V _{CE} =-10V, I _C =-1.0mA	100	-	
		V _{CE} =-10V, I _C =-10mA	100	-	
		V _{CE} =-10V, I _C =-150mA	100	300	
		V _{CE} =-10V, I _C =-500mA	50	-	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-150mA, I _B =-15mA I _C =-500mA, I _B =-50mA		-0.4 -1.6	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =-150mA, I _B =-15mA I _C =-500mA, I _B =-50mA		-1.3 -2.6	V

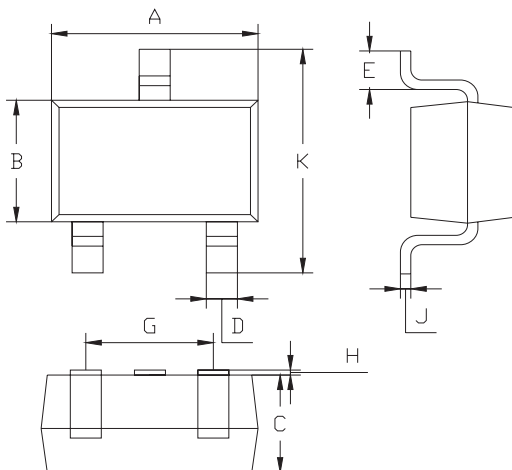
PNP Silicon Epitaxial Planar Transistor



Parameter	Symbol	Test conditions	Min.	Max.	Unit
Transition frequency	f_r	$V_{CE}=-20V, I_C=-50mA$ $f=100MHz$	200		MHz
Collector output capacitance	C_{obo}	$V_{CB}=-10V, I_E=0, f=1MHz$		8	pF
Collector input capacitance	C_{ibo}	$V_{EB}=-2.0V, I_C=0, f=1MHz$		30	pF
Turn-on time	t_{on}	$V_{CC}=-30V, I_C=-150mA,$ $I_{B1}=-15mA$		45	nS
Delay time	t_d			10	nS
Rise time	t_r			40	nS
Turn-off time	t_{off}	$V_{CC}=-6.0V, I_C=-150mA,$ $I_{B1}=I_{B2}=-15mA$		100	nS
Storage time	t_s			80	nS
Fall time	t_f			30	nS

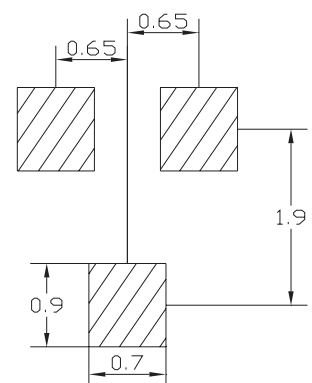
Package Outline

Plastic surface mounted package



SOT-323		
Dim.	Min.	Max.
A	1.8	2.2
B	1.15	1.35
C	1 Typical	
D	0.15	0.35
E	0.25	0.4
G	1.2	1.4
H	0.02	0.1
J	0.1 Typical	
K	2.1	2.3
All Dimensions in mm		

Soldering Footprint



Dimensions : Millimetres

Part Number Table

Description	Part Number
Transistor, Bipolar, PNP, -60V, -600mA, SOT-323	MMST2907A-7-F

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